

MOS FIELD EFFECT TRANSISTOR

2SK3576

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The 2SK3576 is a switching device which can be driven directly by a 2.5 V power source.

The device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5V drive available
- Low on-state resistance

$R_{DS(on)1} = 50 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 2.0 \text{ A)}$

$R_{DS(on)2} = 53 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.0 \text{ V, } I_D = 2.0 \text{ A)}$

$R_{DS(on)3} = 75 \text{ m}\Omega \text{ MAX. (} V_{GS} = 2.5 \text{ V, } I_D = 2.0 \text{ A)}$

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3576	SC-96 (Mini Mold Thin Type)

Marking: XK

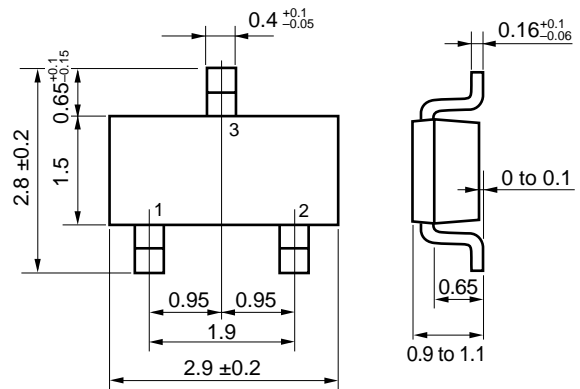
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	20	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 12	V
Drain Current (DC) ($T_A = 25^\circ\text{C}$)	$I_{D(DC)}$	± 4.0	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 16	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T1}	0.2	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{Note2}	P_{T2}	1.25	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes** 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$
 2. Mounted on FR-4 board, $t \leq 5 \text{ sec}$.

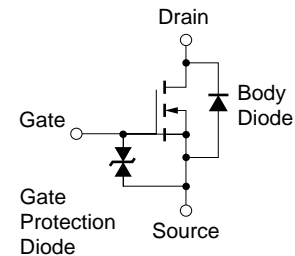
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

PACKAGE DRAWING (Unit: mm)



1 : Gate
 2 : Source
 3 : Drain

EQUIVALENT CIRCUIT



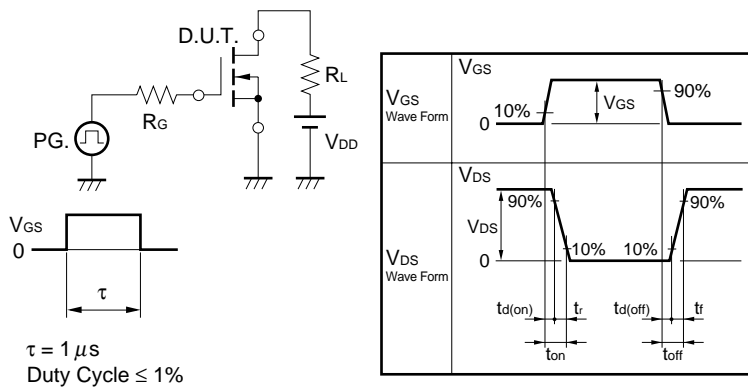
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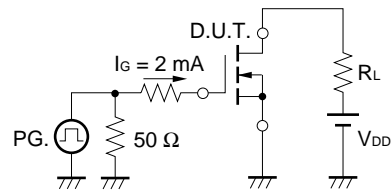
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1.0 mA	0.5		1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 2.0 A	1.0			S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 4.5 V, I _D = 2.0 A		40	50	mΩ
	R _{DS(on)2}	V _{GS} = 4.0 V, I _D = 2.0 A		42	53	mΩ
	R _{DS(on)3}	V _{GS} = 2.5 V, I _D = 2.0 A		56	75	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		250		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		80		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		60		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10 V, I _D = 2.0 A		28		ns
Rise Time	t _r	V _{GS} = 4.0 V		140		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		110		ns
Fall Time	t _f			180		ns
Total Gate Charge	Q _G	V _{DD} = 16 V		3.3		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 4.0 V		0.7		nC
Gate to Drain Charge	Q _{GD}	I _D = 4.0 A		1.5		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 4.0 A, V _{GS} = 0 V		0.89		V

TEST CIRCUIT 1 SWITCHING TIME

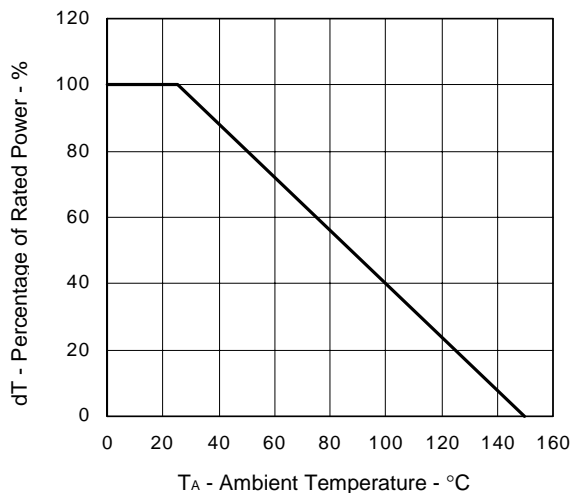


TEST CIRCUIT 2 GATE CHARGE

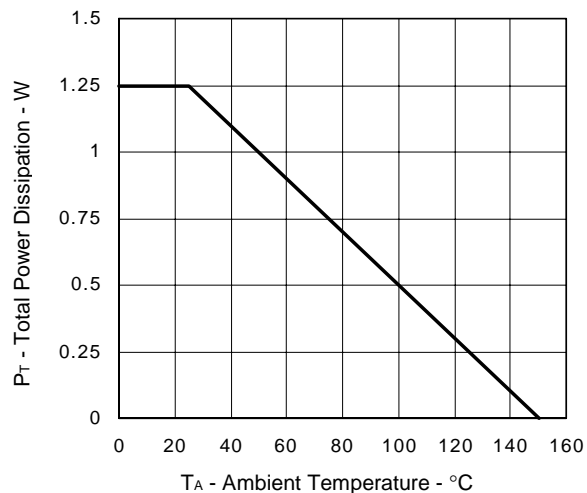


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TYPICAL CHARACTERISTICS (TA = 25°C)

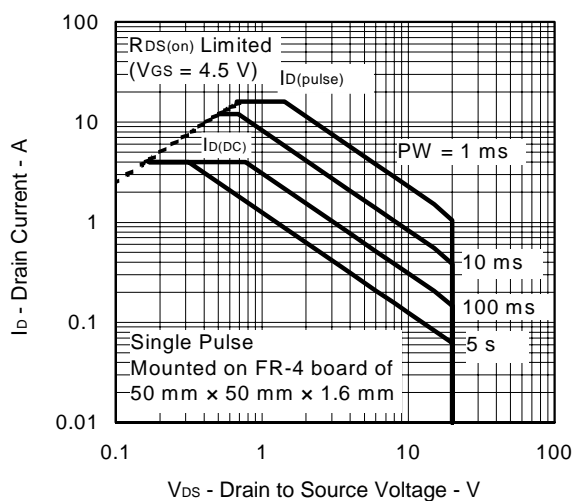
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



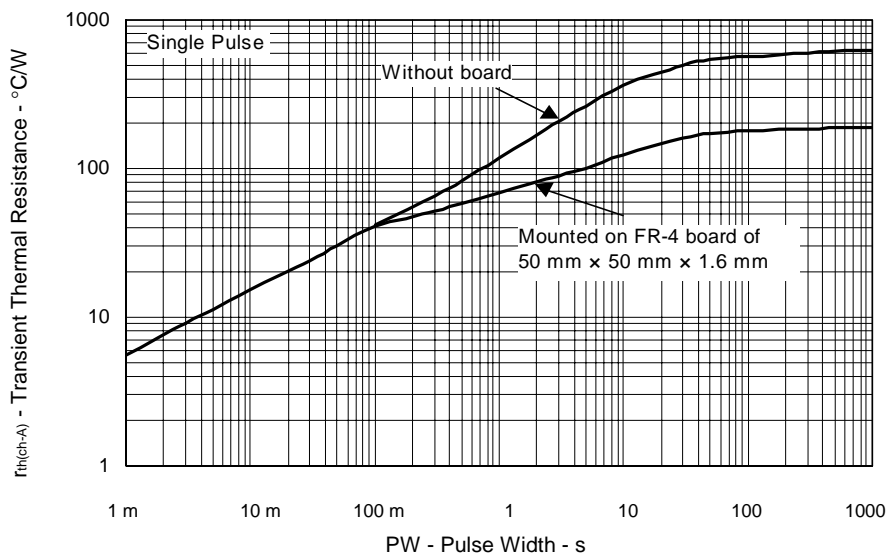
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



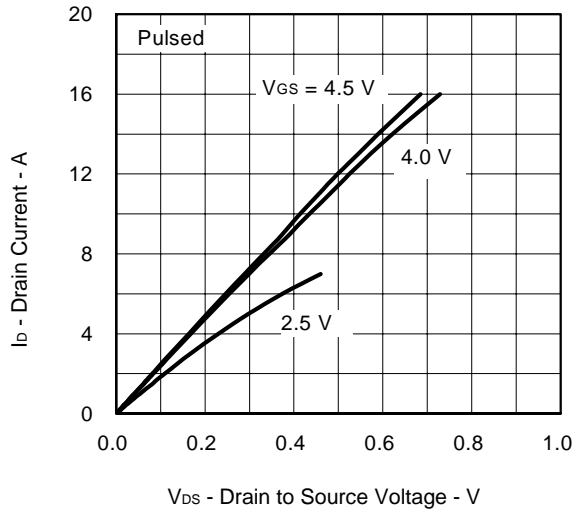
FORWARD BIAS SAFE OPERATING AREA



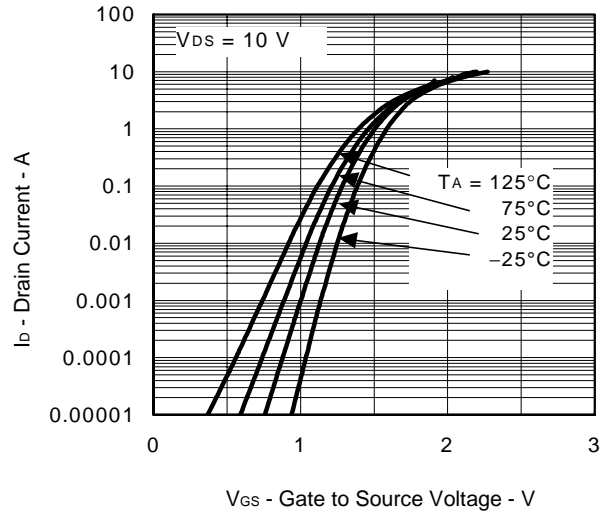
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



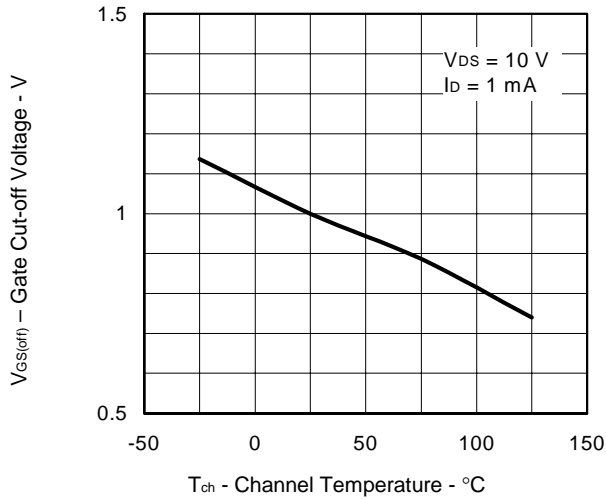
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DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



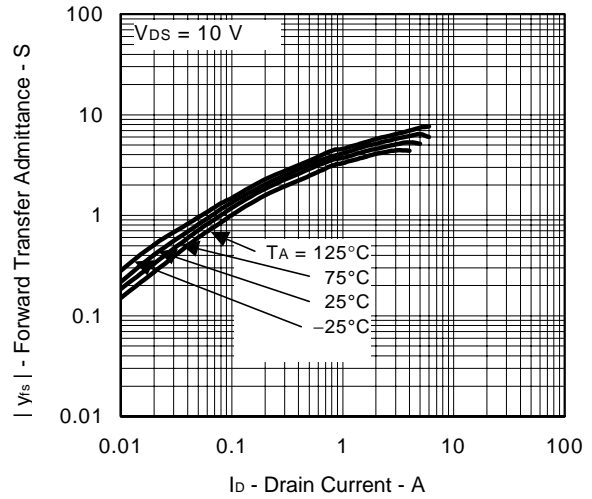
FORWARD TRANSFER CHARACTERISTICS



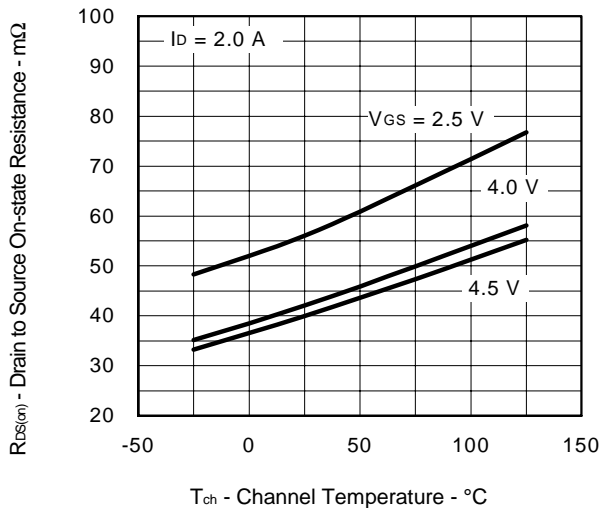
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



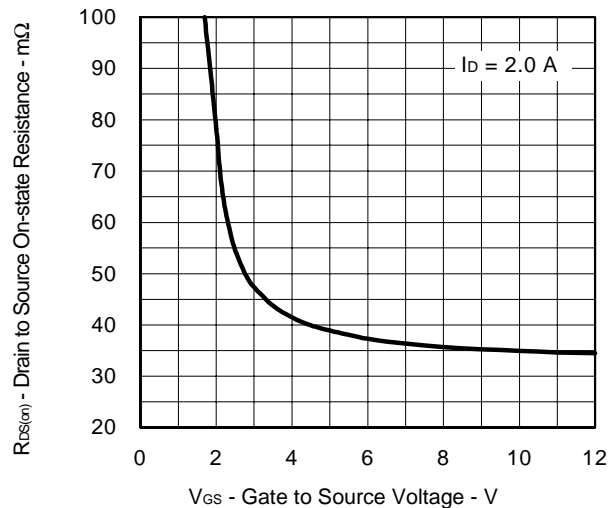
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



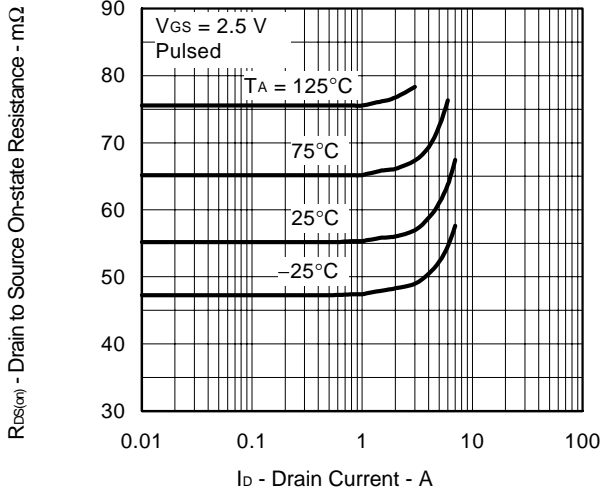
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



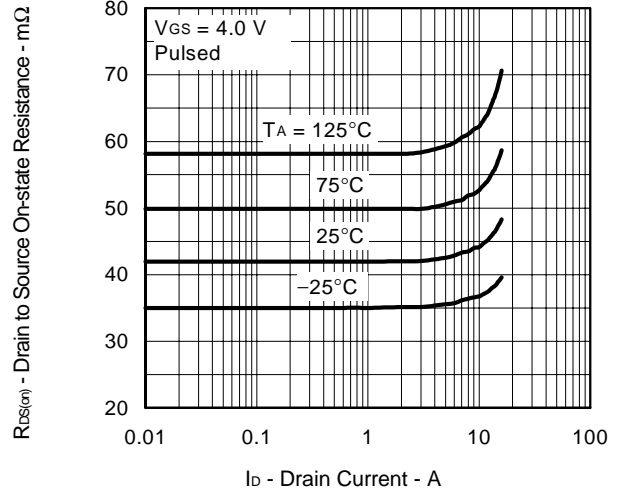
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



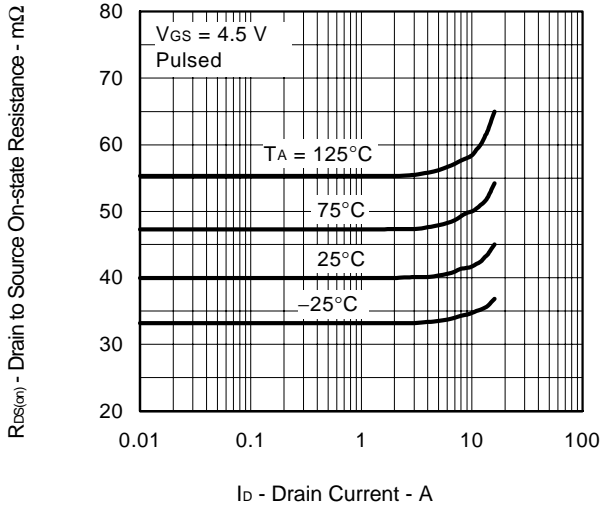
查询"2SK3576"供应商 DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



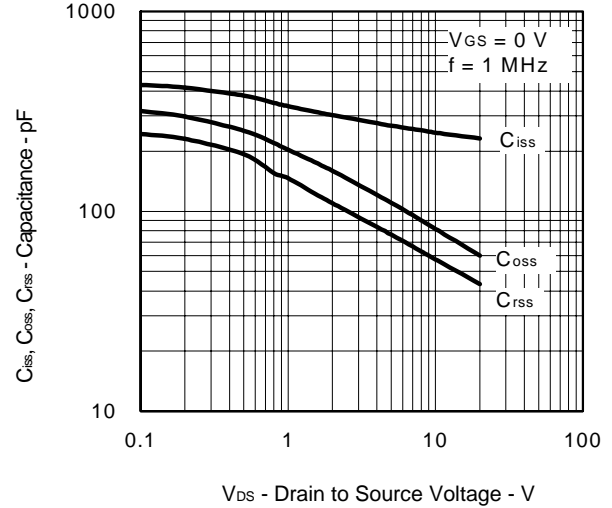
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



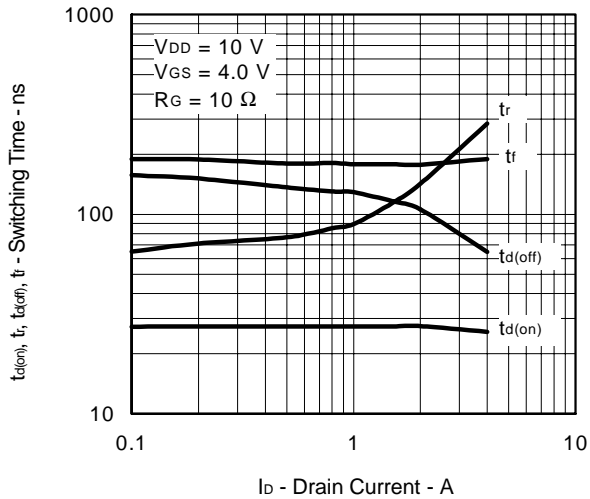
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



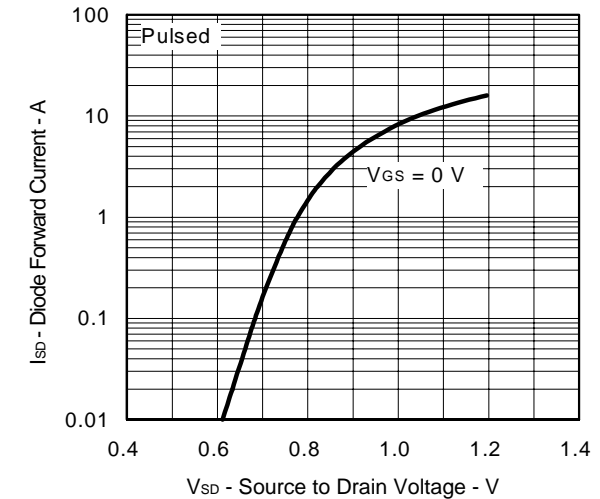
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SWITCHING CHARACTERISTICS

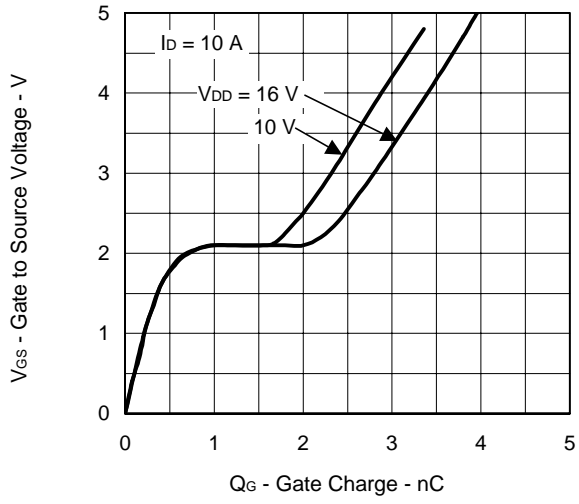


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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DYNAMIC INPUT/OUTPUT CHARACTERISTICS



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